

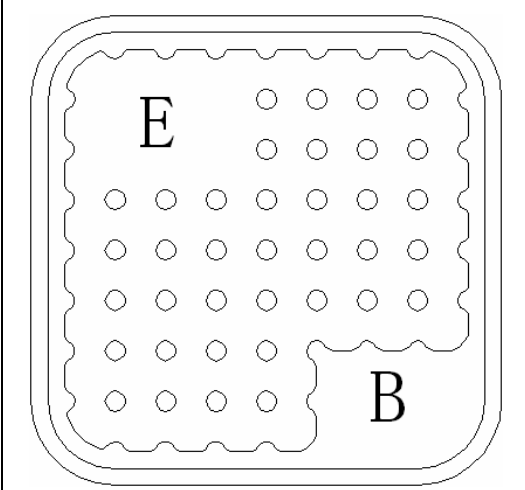
B834A Silicon PNP Epitaxial Transistor

Description: The B834A is designed for audio frequency general amplifier applications and power pumping!

Features: ●Excellent h_{FE} Linearity

●Complementary to D880A

Chip Appearance

	Chip Size		1500um×1500um
	Chip Thickness		210±20um
	Bonding Pad Size	Base	465um×315um
		Emitter	425um×300um
	Front Metal		Al
	Backside Metal		TiNiAg (Au)
	Scribe line width		70um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-50\text{ V}$, $I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5\text{ V}$, $I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c=-100\mu\text{A}$, $I_E=0$	-60		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c=-1\text{ mA}$, $I_B=0$	-60		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu\text{A}$, $I_C=0$	-7		V
DC Current Gain	h_{FE}	$V_{CE}=-5\text{V}$, $I_C=-0.5\text{A}$	100	300	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-3\text{A}$, $I_B=-0.3\text{A}$		-1	V